

九十七學年四技二專第五次聯合模擬考試 電機與電子群 專業科目 (一) 詳解

97-5-03-4
97-5-04-4

1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25
D	B	D	A	B	D	B	A	A	C	B	D	C	C	B	A	D	D	D	D	B	D	D	C	D
26	27	28	29	30	31	32	33	34	35	36	37	38	39	40	41	42	43	44	45	46	47	48	49	50
B	D	C	B	D	C	B	B	C	B	B	C	C	C	C	B	B	B	A	D	B	D	B	B	C

第一部份：基本電學

1. (1) $P_o = 2 \text{ hp} = 2 \times 746 = 1492 \text{ W}$

(2) $P_i = \frac{P_o}{\eta} = \frac{1492}{0.85} \cong 1755 \text{ W}$

(3) $I = \frac{P_i}{V} = \frac{1755}{110} \cong 16 \text{ A}$

2. (1) $R_2 = \rho \frac{\ell_2}{A_2} = \rho \frac{a}{2b^2} = 10 \text{ k}\Omega$

(2) $R_1 = \rho \frac{\ell_1}{A_1} = \rho \frac{2a}{2b^2} = 20 \text{ k}\Omega$

(3) $I = \frac{12}{R_1 + R_2} = \frac{12}{10 \text{ k} + 20 \text{ k}} = 0.4 \text{ mA}$

3. (1) $V_2 = E - V_1 = 15 - 10 = 5 \text{ V}$

(2) $I = \frac{V_2}{R_2} = \frac{5}{50} = 0.1 \text{ A}$

(3) $P_1 = V_1 I = 10 \times 0.1 = 1 \text{ W}$

4. (1) $E = V_1 = V_2 = 12 \text{ V}$

(2) $I_1 R_1 = I_2 R_2 = E = 12 \text{ V}$ ，因 $R_1 = 2R_2$
則 $I_2 = 2I_1 = 4 \text{ mA}$ ，故 $I_1 = 2 \text{ mA}$

(3) $R_2 = \frac{V_2}{I_2} = \frac{12}{4 \text{ mA}} = 3 \text{ k}\Omega$

5. (1) 因 $I_1 = 0$ ，故電橋平衡， $R = 2 \times \frac{8}{4} = 4 \Omega$

(2) $R_{ab} = (8 + 4) // (R + 2) = 12 // 6 = 4 \Omega$

(3) $I = \frac{6}{8 + 4} + \frac{6}{R + 2} = 0.5 + 1 = 1.5 \text{ A}$

6. (1) $V_{3\Omega} = \frac{\frac{12}{6} + \frac{0}{3} + 1}{\frac{1}{6} + \frac{1}{3} + 0} = 6 \text{ V}$

(2) $V_1 = V_{3\Omega} + 1 \times 4 = 6 + 4 = 10 \text{ V}$

7. (1) $V_{BD} = \frac{\frac{14}{1} + \frac{0}{3} + \frac{-6}{6}}{\frac{1}{2} + \frac{1}{3} + \frac{1}{6}} = 6 \text{ V}$

(2) $I_{AB} = \frac{14 - 6}{2} = 4 \text{ A}$

(3) $I_{AC} = \frac{14 - (-6)}{5} = 4 \text{ A}$

(4) $I_1 = I_{AB} + I_{AC} = 4 + 4 = 8 \text{ A}$

(5) $I_{BD} = \frac{V_{BD}}{3} = \frac{6}{3} = 2 \text{ A}$

(6) $I_2 = I_1 - I_{BD} = 8 - 2 = 6 \text{ A}$

(7) $I_3 = I_1 - I_{AB} = 8 - 4 = 4 \text{ A}$

(8) $V_{AB} = I_{AB} \times 2 = 4 \times 2 = 8 \text{ V}$

(9) $V_{AC} = 14 - (-6) = 20 \text{ V}$

8. (1) 求 R_N ：將 6Ω 開路， 12 V 電壓源短路， 1 A 電流源開路， $R_N = 12 \Omega$

(2) 求 V_N ：將 6Ω 短路，使用重疊定理，得
 $I_N = \frac{12}{12} + 1 = 2 \text{ A}$

(3) $I = I_N \frac{R_N}{R_N + 6} = 2 \times \frac{12}{12 + 6} = \frac{4}{3} \text{ A}$

(4) $V_{AB} = 6I = 6 \times \frac{4}{3} = 8 \text{ V}$

9. (1) $R_L = R_{th} = (8 // 8 + 2) // 6 = 3 \Omega$

(2) $V_1 = 24 \times \frac{8 // (6 + 2)}{8 + 8 // (6 + 2)} = 8 \text{ V}$

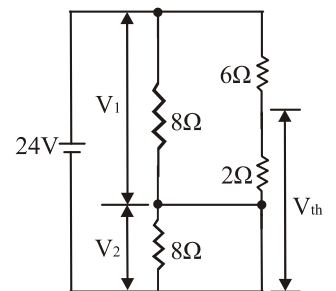
(3) $V_2 = 24 - V_1 = 24 - 8 = 16 \text{ V}$

(4) $V_{th} = V_2 + V_1 \times \frac{2}{2 + 6}$

$= 16 + 8 \times \frac{2}{8} = 18 \text{ V}$

(5) $P_{max} = \left(\frac{V_{th}}{R_{th} + R_L} \right)^2 R_L$

$= \left(\frac{18}{3 + 3} \right)^2 \times 3 = 27 \text{ W}$



10. $C = \epsilon_r \epsilon_0 \frac{A}{d} = 3 \times 8.85 \times 10^{-12} \times \frac{1 \text{ m}^2}{1 \times 10^{-3} \text{ m}} = 26.55 \text{ nF}$

11. (1) $C_T = 12 // (12 + 12) = 8 \mu\text{F}$

(2) $V_{AB} = 20 \times \frac{24}{24 + 12} = \frac{40}{3} \text{ V}$

(3) $Q_T = Q_1 = C_T E = 8 \mu \times 20 = 160 \mu\text{C}$

(4) $Q_2 = Q_3 = \frac{Q_T}{2} = 80 \mu\text{C}$

12. (1) $L_1 + L_2 + 2M = 120$

(2) $L_1 + L_2 - 2M = 80$

(3) 將(1)式-(2)式, 得 $40 \text{ mH} = 4M$, $M = 10 \text{ mH}$

(4) 將(1)式+(2)式, 得 $2(L_1 + L_2) = 200$,

$L_1 + L_2 = 100 \text{ mH}$

(5) 因 $L_1 = 4L_2$, 則 $L_1 + L_2 = 4L_2 + L_2 = 100$, 故 $L_2 = 20 \text{ mH}$, $L_1 = 80 \text{ mH}$

(6) $k = \frac{M}{\sqrt{L_1 L_2}} = \frac{10}{\sqrt{80 \times 20}} = \frac{10}{40} = 0.25$

13. (1) $F = BIl \sin \theta$, 當 $\theta = 90^\circ$ 時, 導線受力最大, 即 $F = 0.1 \times 1 \times 5 = 0.5$ 牛頓

14. (1) 開關 S 接通(ON)瞬間, 電容器視為短路

$i = \frac{16}{4 \text{ k} + 12 \text{ k} / 6 \text{ k}} = 2 \text{ mA}$

$i_C = i \times \frac{12 \text{ k}}{12 \text{ k} + 6 \text{ k}} = 2 \text{ mA} \times \frac{2}{3} = \frac{4}{3} \text{ mA}$

(2) 電路穩定時, 電容器視為開路

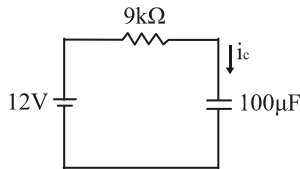
$i = \frac{16}{4 \text{ k} + 12 \text{ k}} = 1 \text{ mA}$, $i_C = 0$

$V_C = 16 \times \frac{12 \text{ k}}{4 \text{ k} + 12 \text{ k}} = 12 \text{ V}$

(3) $\tau = RC = (4 \text{ k} / 12 \text{ k} + 6 \text{ k}) 100 \mu\text{F}$
 $= 0.9 \text{ sec}$

經過一個時間常數後

$V_C = 12 \times 0.632 = 7.584 \text{ V}$



15. (1) $\tau = \frac{L}{R} = \frac{10 \text{ m}}{2} = 5 \text{ mS}$

(2) $i = \frac{E}{R} (1 - e^{-\frac{t}{\tau}}) = \frac{20}{2} (1 - e^{-\frac{t}{5 \text{ m}}}) = 8.65 \text{ A}$

故 $t = 10 \text{ mS}$

16. (1) 平均值 $V_{dc} = 8 \text{ V}$

(2) 有效值 $V_{rms} = \sqrt{8^2 + (\frac{6\sqrt{2}}{\sqrt{2}})^2} = 10 \text{ V}$

17. (1) $X_C = \frac{1}{\omega C} = \frac{1}{10^3 \times 0.1 \mu} = 10 \text{ k}\Omega$

(2) $\bar{Z} = R - jX_C = 10 \text{ k} - j10 \text{ k} = 10\sqrt{2} \angle -45^\circ$

(3) $\bar{V} = 100 \angle 0^\circ$

(4) $\bar{I} = \frac{\bar{V}}{\bar{Z}} = \frac{100 \angle 0^\circ}{10\sqrt{2} \angle -45^\circ} = \frac{10}{\sqrt{2}} \angle 45^\circ$

則 $i(t) = 10 \sin(10^3 t + 45^\circ)$ 毫安

18. (1) $B_L = \frac{1}{\omega L} = \frac{1}{10^3 \times 10 \text{ m}} = 0.1$ 姆歐

(2) $Y = G - jB_L = 0.1 - j0.1 = 0.1\sqrt{2} \angle -45^\circ$ 姆歐

(3) $Z = \frac{1}{Y} = \frac{1}{0.1\sqrt{2}} = 5\sqrt{2}$ 歐姆

(4) $V = \frac{20}{\sqrt{2}} \angle 0^\circ$ 伏特

(5) $I_R = VG = \frac{20}{\sqrt{2}} \times 0.1 = \sqrt{2}$ 安培

(6) $I_L = VB_L = \frac{20}{\sqrt{2}} \times 0.1 = \sqrt{2}$ 安培

(7) $I = VY = \frac{20}{\sqrt{2}} \angle 0^\circ \times 0.1\sqrt{2} \angle -45^\circ = 2 \angle -45^\circ$ 安培

(8) $i(t) = 2\sqrt{2} \sin(10^3 t - 45^\circ)$ 安培

19. (1) $I_1 = \frac{120}{30} - \frac{120}{12} = -6 \text{ A}$

(2) $I = \sqrt{(\frac{120}{15})^2 + (-6)^2} = 10 \text{ A}$

(3) $Z = \frac{E}{I} = \frac{120}{10} = 12 \Omega$

(4) 功率因數 $PF = \frac{G}{Y} = \frac{Z}{R} = \frac{12}{15} = 0.8$

20. (1) $V = \frac{100}{\sqrt{2}} \angle 60^\circ \text{ V}$, $I = \frac{20}{\sqrt{2}} \angle 30^\circ \text{ A}$

(2) $S = VI^* = \frac{100}{\sqrt{2}} \angle 60^\circ \frac{20}{\sqrt{2}} \angle -30^\circ = 1000 \angle 30^\circ$
 $= 500\sqrt{3} + j500 \text{ VA}$

(3) $P = 500\sqrt{3} \text{ W}$, $Q = 500 \text{ VAR}$

(4) $Z = \frac{V}{I} = 5 \angle 30^\circ \Omega$

(5) 電壓 $v(t)$ 相位超前電流 $i(t)$ 相位 30° , 負載為電感性

21. (1) 並聯消耗功率 $P_p = \frac{E^2}{R}$

(2) 串聯消耗功率 $P_s = I^2 R = (\frac{E}{\sqrt{R^2 + X^2}})^2 R$

$= \frac{E^2}{R} (\frac{R}{\sqrt{R^2 + X^2}})^2 = P_p \cos^2 \theta_s$

(3) $P_p = \frac{P_s}{\cos^2 \theta_s} = \frac{320}{0.8^2} = 500 \text{ W}$

22. (1) $f_o = f \sqrt{\frac{X_C}{X_L}} = 1 \text{ k} \sqrt{\frac{500}{20}} = 5 \text{ kHz}$

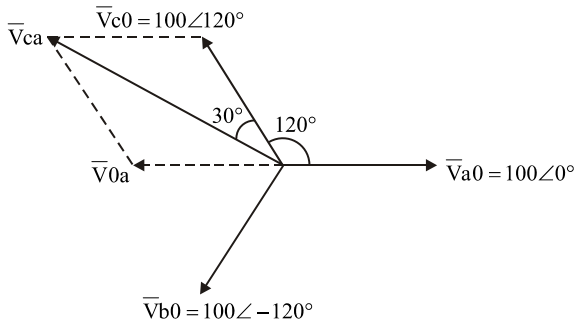
(2) $P = \frac{(\frac{100}{\sqrt{2}})^2}{10} = 500 \text{ W}$

23. (1) 電容電壓相位滯後電路電流相位 90°

(2) 電感電壓相位超前電路電流相位 90°

24. $I_L = \frac{P_o}{\sqrt{3} V_L \cos \theta} = \frac{5 \times 746}{\sqrt{3} \times 220 \times 0.8} = 12.2 \text{ A}$

25.



第二部份：電子學

26. (1) 最大值 $V_m = 100 \text{ V}$

(2) $t = \frac{1}{180}$ 秒時的瞬間值

$$v(t) = 100 \sin(2\pi \times 60 \times \frac{1}{180} + 60^\circ) = 100 \sin(180^\circ) = 0$$

(3) $f = \frac{\omega}{2\pi} = \frac{377}{2\pi} = 60 \text{ Hz}$

(4) 電壓信號 $v(t) = 100 \sin(377t + 60^\circ)$ 與電流信號 $i(t) = 10 \cos(377t - 30^\circ) = 10 \sin(377t + 60^\circ)$ 相位差 $\theta = 60^\circ - 60^\circ = 0^\circ$

27. (A) 電洞濃度 $p \cong N_A = \frac{5 \times 10^{22}}{10^8} = 5 \times 10^{14} / \text{cm}^3$

(B) 電子濃度

$$n = \frac{n_i^2}{N_A} = \frac{(1.5 \times 10^{10})^2}{5 \times 10^{14}} = 4.5 \times 10^5 / \text{cm}^3$$

(C) 本質半導體、P 型半導體及 N 型半導體中的電子數目等於質子數目，電性為中性

(D) 多數載子為電洞，少數載子為電子

28. (1) $I_S = \frac{E - V_Z}{R_S} = \frac{12 - 6}{1 \text{ k}} = 6 \text{ mA}$

(2) $I_{L(\text{max})} = I_S - I_{ZK} = 6 - 1 = 5 \text{ mA}$

(3) $R_{L(\text{min})} = \frac{V_Z}{I_{L(\text{max})}} = \frac{6}{5 \text{ mA}} = 1.2 \text{ k}\Omega$

29. (1) 次級 $V_m = 40 \times \frac{1}{2} \times \frac{1}{2} = 10 \text{ V}$

(2) $V_{dc} = 0.636 V_m = 0.636 \times 10 = 6.36 \text{ V}$

(3) $\text{PIV} = 2 V_m = 2 \times 10 = 20 \text{ V}$

30. (1) $V_{r(\text{rms})} = \frac{4.8}{R_L C} V_{dc} = \frac{4.8}{10 \times 100} \times 10 = 48 \text{ mV}$

(2) $V_{r(\text{P-P})} = 2\sqrt{3} V_{r(\text{rms})} = 2 \times 1.732 \times 48 \text{ mV} = 166 \text{ mV}$

31. (1) 當 $V_i \leq -2 \text{ V}$ 時，二極體導通， $V_o = -2 \text{ V}$

(2) 當 $V_i > -2 \text{ V}$ 時，二極體截止， $V_o = V_i$

32. (1) 射極摻雜濃度最高，但逆向耐壓最低

(2) 集極摻雜濃度最低，但逆向耐壓最高

33. NPN 電晶體操作在主動區時， $V_{BE} > 0$ ， $V_{BC} < 0$ ， $V_{CE} > 0$ ，則 $V_C > V_B > V_E$

34. (1) $I_{C(\text{sat})} = \frac{V_{CC} - V_{CE(\text{sat})}}{R_C} = \frac{5 - 0.2}{R_C} = \frac{4.8}{R_C}$

(2) $I_B = \frac{V_{BB} - V_{BE}}{R_B} = \frac{2.7 - 0.7}{R_B} = \frac{2}{R_B}$

(3) 飽和條件： $\beta I_B \geq I_{C(\text{sat})}$ ，則 $100 \times \frac{2}{R_B} \geq \frac{4.8}{R_C}$

故 $R_B \leq 41.6 R_C$

35. (1) 減少 I_C 值，可以使工作點由飽和區附近移向直線負載線中央，因 $I_B = \frac{V_{CC} - V_{BE}}{R_B}$ ， $I_C = \beta I_B$ ，故

增加 R_B 值即可減少 I_C

36. (1) $I_B = \frac{0 - 0.7 - (-12)}{565 \text{ k}} = 0.02 \text{ mA}$

(2) $I_C = \beta I_B = 100 \times 0.02 \text{ mA} = 2 \text{ mA}$

(3) $0 - V_{EC} - (-12) = I_C R_C$
則 $V_{EC} = 12 - I_C R_C = 12 - 2 \text{ mA} \times 2 \text{ k} = 8 \text{ V}$

故 $V_{CE} = -V_{EC} = -8 \text{ V}$

(4) $V_B = V_{BE} = -V_{EB} = -0.7 \text{ V}$

(5) $I_{C(\text{sat})} = \frac{12 - 0.2}{2 \text{ k}} = 5.9 \text{ mA}$ ，因 $\beta I_B > I_{C(\text{sat})}$

故 BJT 工作於主動區

37. (1) $I_{C(\text{sat})} \cong \frac{V_{CC}}{R_C + R_E} = \frac{12}{5 \text{ k} + 1 \text{ k}} = 2 \text{ mA}$

(2) $I_B = \frac{V_{CC} - V_{BE}}{R_B + (1 + \beta)R_E} = \frac{12 - 0.7}{200 \text{ k} + 101 \text{ k}} = 37.5 \mu\text{A}$

因 $\beta I_B > I_{C(\text{sat})}$ ，電晶體已飽和，故需重新計算 I_B 值

(3) $V_{CC} = V_{BE} + I_B R_B + I_E R_E$
 $= V_{BE} + I_B R_B + (I_B + I_{C(\text{sat})}) R_E$

則 $I_B = \frac{V_{CC} - V_{BE} - I_{C(\text{sat})} R_E}{R_B + R_E} = \frac{12 - 0.7 - 2 \text{ mA} \times 1 \text{ k}}{200 \text{ k} + 1 \text{ k}} = 46.3 \mu\text{A}$

38. (1) $\frac{V_o}{V_s} = \frac{V_i}{V_s} \frac{V_o}{V_i} = -\beta \frac{r_\pi}{R_s + r_\pi} \frac{R_C // R_L}{r_\pi} = -100 \times \frac{2 \text{ k}}{0.5 \text{ k} + 2 \text{ k}} \frac{4 \text{ k} // 12 \text{ k}}{2 \text{ k}} = -120$

39. (1) $I_E \cong \frac{V_{CC} - V_{CE}}{R_C + R_E} = \frac{12 - 6}{4.7 \text{ k} + 1.3 \text{ k}} = 1 \text{ mA}$

(2) $V_T = \frac{(273.2 + 27)}{11600} = 25.8 \text{ mV}$

(3) $r_e = \frac{V_T}{I_E} = \frac{25.8}{1} \cong 26 \Omega$

(4) $\frac{V_o}{V_i} = -\frac{R_C}{r_e} = -\frac{4.7 \text{ k}}{26} = -180$

40. (1) $I_2 = \frac{V_B}{R_{B2}} = \frac{V_{BE} + V_E}{R_{B2}} = \frac{0.7 + 1.3}{5 \text{ k}} = 0.4 \text{ mA}$

$$(2) I_1 = I_2 + I_B \cong I_2 = \frac{V_{CC} - V_B}{R_{B1}}$$

$$\text{故 } R_{B1} = \frac{V_{CC} - V_B}{I_1} = \frac{24 - 2}{0.4 \text{ m}} = 55 \text{ k}\Omega$$

(3) 因 R_{B2} 開路

$$\text{故 } I_B = \frac{V_{CC} - V_{BE}}{R_{B1} + (1 + \beta)R_E} = \frac{24 - 0.7}{55 \text{ k} + 201 \times 1.3 \text{ k}} = 73.6 \text{ }\mu\text{A}$$

$$(4) I_{C(\text{sat})} = \frac{V_{CC} - V_{CE(\text{sat})}}{R_C + R_E} = \frac{24 - 0.2}{4.7 \text{ k} + 1.3 \text{ k}} = 4 \text{ mA}$$

(5) 因 $\beta I_B > I_{C(\text{sat})}$ ，故電晶體工作於飽和區

$$41. (1) A_{i(\text{dB})} = 20 \log A_i = 20 \log 10 = 20 \text{ dB}$$

$$(2) A_{p(\text{dB})} = \frac{1}{2}(A_{v(\text{dB})} + A_{i(\text{dB})}) = 40$$

$$\text{故 } A_{v(\text{dB})} = 80 - A_{i(\text{dB})} = 80 - 20 = 60 \text{ dB}$$

$$(3) A_{v(\text{dB})} = 20 \log A_v = 60, \text{ 故 } A_v = 1000$$

$$(4) A_v = A_{v1}A_{v2}, \text{ 故 } A_{v2} = \frac{A_v}{A_{v1}} = \frac{1000}{-100} = -10$$

$$42. (1) I_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_{GS(\text{off})}}\right)^2 = 16 \times \left(1 - \frac{V_{GS}}{-4}\right)^2$$

$$(2) V_{GS} = V_G - V_S = -I_D R_S = -I_D (0.5)$$

解(1)(2)聯立方程式，得 $V_{GS} = -2 \text{ V}$ ， $I_D = 4 \text{ mA}$

(3) JFET 工作於定電流區的條件：

$$V_{DG} \geq |V_{GS(\text{off})}| = 4$$

$$\text{則 } V_{DG} = V_D - V_G = V_{DD} - I_D R_D - 0 \geq 4$$

$$\text{故 } R_D \leq \frac{V_{DD} - 4}{I_D} = \frac{12 - 4}{4 \text{ m}} = 2 \text{ k}\Omega$$

43. (1) 對空乏型 FET 元件而言， $V_{GS} = 0$ 時，

$$I_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_{GS(\text{off})}}\right)^2, \text{ 因 } V_{GS} \text{ 可正、可負，故 } I_D$$

的最大值將會大於 I_{DSS}

$$44. (1) I_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_{GS(\text{off})}}\right)^2 = 8 \times \left(1 - \frac{V_{GS}}{-4}\right)^2$$

$$(2) V_{GS} = V_G - V_S = -I_D R_S = -I_D (0.5 + 0.5)$$

解(1)(2)聯立方程式，得 $V_{GS} = -2 \text{ V}$ ， $I_D = 2 \text{ mA}$

$$(3) R_D = \frac{V_{DD} - V_{DS} - I_D R_S}{I_D}$$

$$= \frac{24 - 12 - 2 \text{ m} \times 1 \text{ k}}{2 \text{ m}} = 5 \text{ k}\Omega$$

$$(4) g_m = \frac{2I_{DSS}}{|V_{GS(\text{off})}|} \left(1 - \frac{V_{GS}}{V_{GS(\text{off})}}\right)$$

$$= \frac{2 \times 8}{4} \left(1 - \frac{-2}{-4}\right) = 2 \text{ mA/V}$$

$$(5) \frac{V_o}{V_i} = -\frac{R_D}{\frac{1}{g_m} + R_{S1}} = -\frac{5 \text{ k}}{\frac{1}{2 \text{ m}} + 500} = -5$$

$$45. (1) \frac{V_o}{V_i} = -\frac{100}{10} = -10$$

(2) $V_o = -10V_i = 10 \times 2 = -20 \text{ V}$ ，因 V_o 已超過電源電壓，輸出已飽和， $V_o = -12 \text{ V}$

$$46. (1) \frac{V_o}{V_i} = -\frac{100}{20} \times \left(1 + \frac{R}{50}\right) = -\frac{12}{1} = -12$$

故 $R = 70 \text{ k}\Omega$

$$47. (1) \frac{\sin \theta}{\sin 90^\circ} = \frac{1}{2}, \text{ 則 } \theta = 30^\circ$$

(2) 工作週期

$$= \frac{180^\circ + 2\theta}{360^\circ} \times 100\% = \frac{180^\circ + 60^\circ}{360^\circ} \times 100\% = 66\%$$

$$48. (1) \text{ 通帶電壓增益 } A_v = 1 + \frac{R_2}{R_1} = 1 + \frac{90 \text{ k}}{10 \text{ k}}$$

則 $A_{v(\text{dB})} = 20 \log 10 = 20 \text{ dB}$

$$(2) f_L = \frac{1}{2\pi RC} = \frac{1}{2\pi \times 10 \text{ k} \times 0.1 \mu} = 159 \text{ Hz}, \text{ 截止點}$$

增益為 $20 \text{ dB} - 3 \text{ dB} = 17 \text{ dB}$

$$(3) \text{ 截止帶電壓增益 } A_v = \frac{V_o}{V_i} \cong \frac{f}{f_L} \left(1 + \frac{R_2}{R_1}\right)$$

$$20 \log A_v = 20 \log \left(\frac{f}{f_L}\right) + 20 \log \left(1 + \frac{R_2}{R_1}\right)$$

$$= 20 \log \left(\frac{f}{159}\right) + 20 \text{ dB}$$

(4) 當 $f = 15.9 \text{ Hz}$ 時，

$$20 \log \left(\frac{f}{159}\right) + 20 \text{ dB} = 20 \log \left(\frac{15.9}{159}\right) + 20$$

$$= -20 + 20 = 0 \text{ dB}$$

(5) 當 $f = 1.59 \text{ kHz}$ 時，增益為 20 dB

$$50. T = 2RC \ln \left(1 + \frac{2R_1}{R_2}\right)$$